



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN *et al.* Confirmation No.: 7326
Application No.: 10/614,327 Group Art Unit: 2822
Filing Date: July 8, 2003 Examiner: M. Wilczewski
For: TRANSFER OF A THIN LAYER FROM A Attorney Docket No.: 4717-7600
WAFER COMPRISING A BUFFER
LAYER

SECOND INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed is a Form PTO-1449 listing four (4) references for the Examiner's review.

Copies of these references, B1 and C1-C3, are enclosed herewith.

It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the these references. Should any fees be required, however, please charge such fees to Winston & Strawn LLP Deposit Account No. 50-1814.

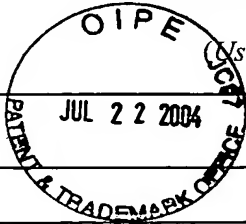
Respectfully submitted,

July 22, 2004
Date

E. Bradley Gould (Reg. No. 41,792)
For: Allan A. Fanucci (Reg. No. 30,256)

WINSTON & STRAWN LLP
Customer No. 28765

202-371-5771

LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 <i>(Use several sheets if necessary)</i>				ATTY. DOCKET NO.: 4717-7600		APPLICATION NO.: 10/614,327	
				APPLICANT: Bruno GHYSELEN et al.			
				FILING DATE: July 8, 2003		GROUP: 2822	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	<div style="text-align: center;">TRANSLATION</div> <div style="display: flex; justify-content: space-around; font-size: small;"> YES NO </div>
	B1	10-209453	08/1988	JP (w/English abstract)			X
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
	C1	E.A. Fitzgerald et al., <i>Relaxed Ge_xSi_{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si</i> ; <u>J.Vac.Sci.Technol</u> ; B 10(4), Jul/Aug 1992; pp. 1807-1819.					
	C2	R. Egloff et al., <i>Evaluation of Strain Sources in Bond and Etchback Silicon-on-Insulator</i> ; <u>Philips Journal of Research</u> ; Vol. 49, No. 1/2 1995; pp125-138.					
	C3	Cher Ming Tan et al., <i>Temperature and Stress Distribution in the SOI Structure During Fabrication</i> ; <u>ZIEEE Transactions on Semiconductor Manufacturing</u> , Vol. 16, No. 2, May 2003; pp. 314-317.					
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							